

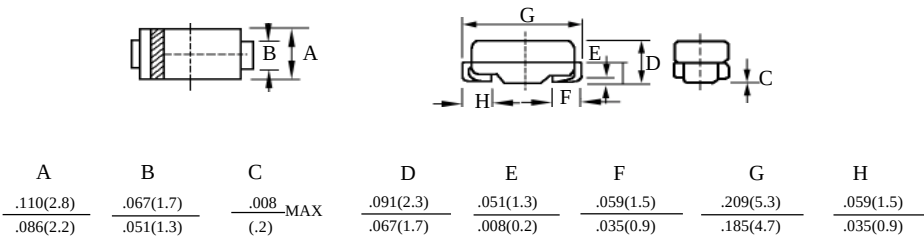


EFM101 – EFM106

1A 片式快速二极管
 1A FAST RECOVERY SMA DIODES

型 号 TYPE	印 字 Marking	反 向 重 复 峰 值 电 压 $V_{RRM}(V)$	正 向 平 均 电 流 $I_F(A)$	正 向 峰 值 电 压 $V_F(V)$	反 向 峰 值 电 流 $I_{RM}(\mu A)$	正 向 浪 涌 电 流 $I_{P8M}(A)$	反 向 恢 复 时 间 $T_{rr}(ns)$	外形尺寸 Package Dimensions
EFM101	EF1	50	1.0	0.95	5.0	30	35	DO – 214AC
EFM102	EF2	100		0.95				
EFM103	EF3	150		0.95				
EFM104	EF4	200		0.95				
EFM105	EF5	300		1.25				
EFM106	EF6	400		1.25				

Trr测试条件: $I_F=1A$, $I_R=0.5A$, $I_{RR}=0.25A$
 Trr Test Conditions: $I_F=1A$, $I_R=0.5A$, $I_{RR}=0.25A$

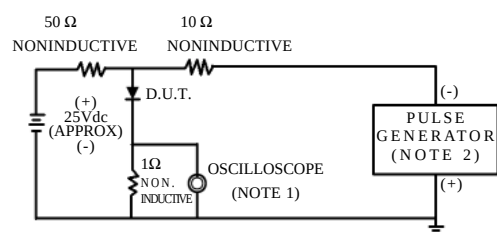


DO – 214AC

EFM101 –EFM106

1A 片式快速二极管额定值与特性曲线

RATING & CHARACTERISTIC CURVES OF 1A FAST RECOVERY SMA DIODES

 FIG.1-TEST CIRCUIT DIAGRAM AND
REVERSE RECOVERY TIME CHARACTERISTIC


NOTES:1.Rise Time=7ns max.
Input Impedance=1megohm.22pF.
2.Rise Time=10ns max.
Source Impedance=50 ohms.

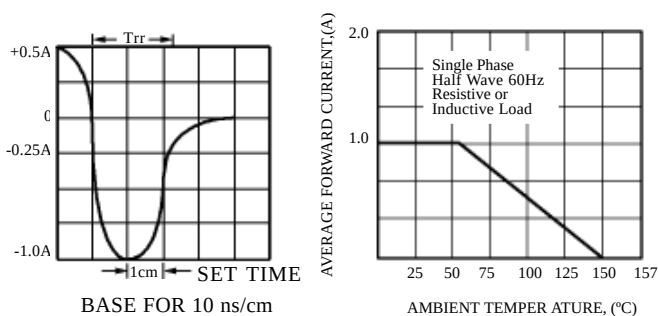
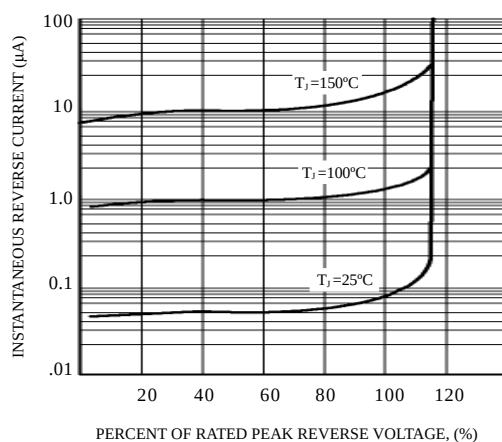
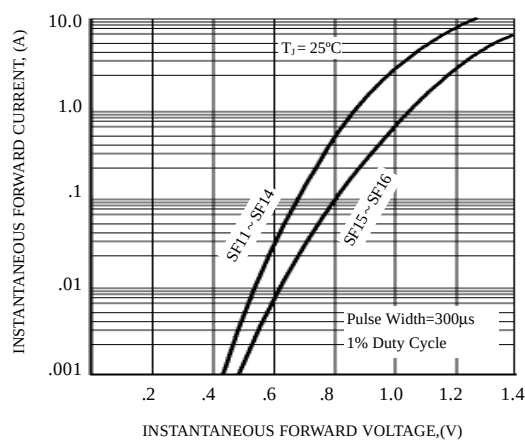
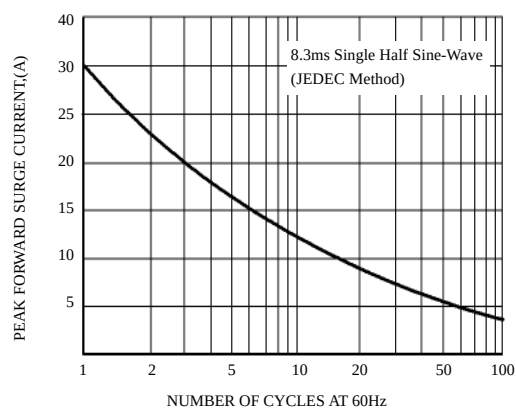
 FIG. 2 - TYPICAL FORWARD
CURRENT DERATING CURVE

 FIG. 3 - TYPICAL REVERSE
CHARACTERISTICS

 FIG. 4 - TYPICAL INSTANTANEOUS
FORWARD CHARACTERISTICS

 FIG. 5 - MAXIMUM NON-REPETITIVE
FORWARD SURGE CURRENT


FIG. 6 - TYPICAL JUNCTION CAPACITANCE

